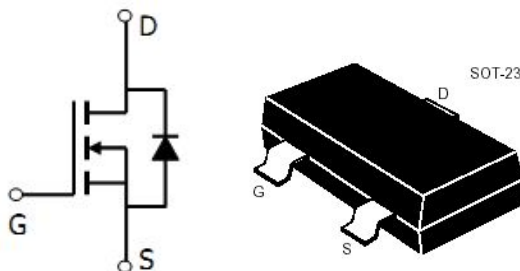


GML2402

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)


N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	20	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 12	V
Drain Current (continuous) 漏極電流-連續	I_D	1.2	A
Drain Current (pulsed) 漏極電流-脉冲	I_{DM}	5	A
Total Device Dissipation 總耗散功率 $T_A=25^{\circ}\text{C}$ 環境溫度為 25°C	P_D	540	mW
Junction 結溫	T_J	150	$^{\circ}\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55to+150	$^{\circ}\text{C}$

■DEVICE MARKING 打標
GML2402=A402

GML2402

■ ELECTRICAL CHARACTERISTICS 電特性

 (T_A=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D = 250uA, V _{GS} =0V)	BV _{DSS}	20	—	—	V
Gate Threshold Voltage 柵極開啓電壓(I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	0.7	—	—	V
Drain-Source On Voltage 漏極-源極導通電壓(I _D = 50mA, V _{GS} = 5V) (I _D = 500mA, V _{GS} = 10V)	V _{DS(ON)}	—	—	0.375 3.75	V
Diode Forward Voltage Drop 內附二極管正向壓降(I _S = 0.75A, V _{GS} =0V)	V _{SD}	—	—	1.2	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V _{GS} =0V, V _{DS} = 16V) (V _{GS} =0V, V _{DS} = 16V, T _A =55°C)	I _{DSS}	—	—	1 10	uA
Gate Body Leakage 柵極漏電流(V _{GS} =±12V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I _D =1.2A, V _{GS} =4.5V) (I _D =1A, V _{GS} =2.5V)	R _{DS(ON)}	—	—	250 350	mΩ
Input Capacitance 輸入電容 (V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{ISS}	—	—	310	pF
Common Source Output Capacitance 共源輸出電容(V _{GS} =0V, V _{DS} = 6V, f=1MHz)	C _{OSS}	—	—	80	pF
Turn-ON Time 開啓時間 (V _{DS} = 10V, I _D = 1A, R _{GEN} =6Ω)	t _(on)	—	—	15	ns
Turn-OFF Time 關斷時間 (V _{DS} = 10V, I _D = 1A, R _{GEN} =6Ω)	t _(off)	—	—	20	ns

Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%